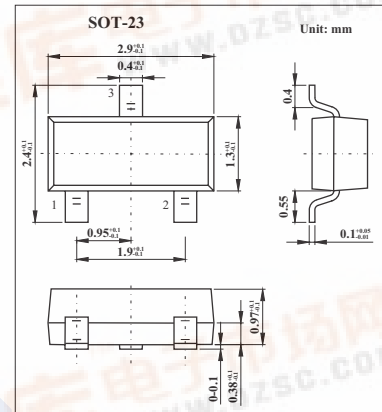
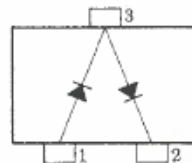


SMD Type Diodes

Schottky Barrier Diode  
1SS358

Features

- Small interterminal capacitance
- Low forward voltage and excellent detection efficiency
- High breakdown voltage



Absolute Maximum Ratings Ta = 25°C

| Parameter                 | Symbol           | Rating       | Unit |
|---------------------------|------------------|--------------|------|
| peak reverse voltage      | V <sub>R</sub>   | 55           | V    |
| Forward current           | I <sub>F</sub>   | 10           | mA   |
| Power dissipation         | P                | 150          | mW   |
| Junction Temperature      | T <sub>j</sub>   | 125          | °C   |
| Storage Temperature range | T <sub>stg</sub> | -55 to + 125 | °C   |

Electrical Characteristics Ta = 25°C

| Parameter                 | Symbol         | Test Conditions                 | Min | Typ  | Max  | Unit |
|---------------------------|----------------|---------------------------------|-----|------|------|------|
| Forward voltage           | V <sub>F</sub> | I <sub>F</sub> = 1 mA           |     |      | 0.35 | V    |
| Reverse voltage           | V <sub>R</sub> | I <sub>R</sub> = 100 μ A        | 55  |      |      | V    |
| Forward Current           | I <sub>F</sub> | V <sub>F</sub> = 1V             | 10  |      |      | mA   |
| Reverse current           | I <sub>R</sub> | V <sub>R</sub> = 40V            |     |      | 50   | μ A  |
| Interterminal capacitance | C              | V <sub>R</sub> = 0, f = 1.0 MHz |     | 0.45 |      | pF   |

Marking

|         |    |
|---------|----|
| Marking | DH |
|---------|----|